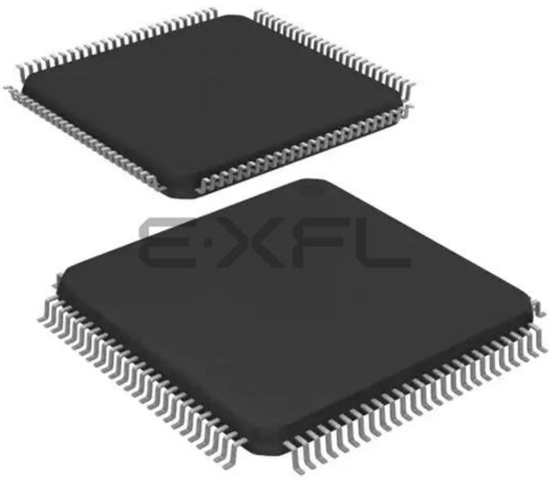

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M4F
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	EBI/EMI, I²C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	85
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32wg280f128-qfp100

available in EM2. This makes it ideal for keeping track of time since the RTC is enabled in EM2 where most of the device is powered down.

2.1.19 Backup Real Time Counter (BURTC)

The Backup Real Time Counter (BURTC) contains a 32-bit counter and is clocked either by a 32.768 kHz crystal oscillator, a 32.768 kHz RC oscillator or a 1 kHz ULFRCO. The BURTC is available in all Energy Modes and it can also run in backup mode, making it operational even if the main power should drain out.

2.1.20 Low Energy Timer (LETIMER)

The unique LETIMER^{TM}, the Low Energy Timer, is a 16-bit timer that is available in energy mode EM2 in addition to EM1 and EM0. Because of this, it can be used for timing and output generation when most of the device is powered down, allowing simple tasks to be performed while the power consumption of the system is kept at an absolute minimum. The LETIMER can be used to output a variety of waveforms with minimal software intervention. It is also connected to the Real Time Counter (RTC), and can be configured to start counting on compare matches from the RTC.

2.1.21 Pulse Counter (PCNT)

The Pulse Counter (PCNT) can be used for counting pulses on a single input or to decode quadrature encoded inputs. It runs off either the internal LFACLK or the PCNTn_S0IN pin as external clock source. The module may operate in energy mode EM0 – EM3.

2.1.22 Analog Comparator (ACMP)

The Analog Comparator is used to compare the voltage of two analog inputs, with a digital output indicating which input voltage is higher. Inputs can either be one of the selectable internal references or from external pins. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

2.1.23 Voltage Comparator (VCMP)

The Voltage Supply Comparator is used to monitor the supply voltage from software. An interrupt can be generated when the supply falls below or rises above a programmable threshold. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

2.1.24 Analog to Digital Converter (ADC)

The ADC is a Successive Approximation Register (SAR) architecture, with a resolution of up to 12 bits at up to one million samples per second. The integrated input mux can select inputs from 8 external pins and 6 internal signals.

2.1.25 Digital to Analog Converter (DAC)

The Digital to Analog Converter (DAC) can convert a digital value to an analog output voltage. The DAC is fully differential rail-to-rail, with 12-bit resolution. It has two single ended output buffers which can be combined into one differential output. The DAC may be used for a number of different applications such as sensor interfaces or sound output.

2.1.26 Operational Amplifier (OPAMP)

The EFM32WG280 features 3 Operational Amplifiers. The Operational Amplifier is a versatile general purpose amplifier with rail-to-rail differential input and rail-to-rail single ended output. The input can be set to pin, DAC or OPAMP, whereas the output can be pin, OPAMP or ADC. The current is programmable and the OPAMP has various internal configurations such as unity gain, programmable gain using internal resistors etc.

Module	Configuration	Pin Connections
PRS	Full configuration	NA
EBI	Full configuration	EBI_A[27:0], EBI_AD[15:0], EBI_ARDY, EBI_ALE, EBI_BL[1:0], EBI_CS[3:0], EBI_CSTFT, EBI_DCLK, EBI_DTEN, EBI_HSNC, EBI_NANDREn, EBI_NANDWEn, EBI_REn, EBI_VSNC, EBI_WEn
I2C0	Full configuration	I2C0_SDA, I2C0_SCL
I2C1	Full configuration	I2C1_SDA, I2C1_SCL
USART0	Full configuration with IrDA	US0_TX, US0_RX. US0_CLK, US0_CS
USART1	Full configuration with I2S	US1_TX, US1_RX, US1_CLK, US1_CS
USART2	Full configuration with I2S	US2_TX, US2_RX, US2_CLK, US2_CS
UART0	Full configuration	U0_TX, U0_RX
UART1	Full configuration	U1_TX, U1_RX
LEUART0	Full configuration	LEU0_TX, LEU0_RX
LEUART1	Full configuration	LEU1_TX, LEU1_RX
TIMER0	Full configuration with DTI	TIM0_CC[2:0], TIM0_CDTI[2:0]
TIMER1	Full configuration	TIM1_CC[2:0]
TIMER2	Full configuration	TIM2_CC[2:0]
TIMER3	Full configuration	TIM3_CC[2:0]
RTC	Full configuration	NA
BURTC	Full configuration	NA
LETIMER0	Full configuration	LET0_O[1:0]
PCNT0	Full configuration, 16-bit count register	PCNT0_S[1:0]
PCNT1	Full configuration, 8-bit count register	PCNT1_S[1:0]
PCNT2	Full configuration, 8-bit count register	PCNT2_S[1:0]
ACMP0	Full configuration	ACMP0_CH[7:0], ACMP0_O
ACMP1	Full configuration	ACMP1_CH[7:0], ACMP1_O
VCMP	Full configuration	NA
ADC0	Full configuration	ADC0_CH[7:0]
DAC0	Full configuration	DAC0_OUT[1:0], DAC0_OUTxALT
OPAMP	Full configuration	Outputs: OPAMP_OUTx, OPAMP_OUTxALT, Inputs: OPAMP_Px, OPAMP_Nx
AES	Full configuration	NA
GPIO	85 pins	Available pins are shown in Table 4.3 (p. 67)

2.3 Memory Map

The *EFM32WG280* memory map is shown in Figure 2.2 (p. 9), with RAM and Flash sizes for the largest memory configuration.

3 Electrical Characteristics

3.1 Test Conditions

3.1.1 Typical Values

The typical data are based on T_{AMB}=25°C and V_{DD}=3.0 V, as defined in Table 3.2 (p. 10), by simulation and/or technology characterisation unless otherwise specified.

3.1.2 Minimum and Maximum Values

The minimum and maximum values represent the worst conditions of ambient temperature, supply voltage and frequencies, as defined in Table 3.2 (p. 10), by simulation and/or technology characterisation unless otherwise specified.

3.2 Absolute Maximum Ratings

The absolute maximum ratings are stress ratings, and functional operation under such conditions are not guaranteed. Stress beyond the limits specified in Table 3.1 (p. 10) may affect the device reliability or cause permanent damage to the device. Functional operating conditions are given in Table 3.2 (p. 10) .

Table 3.1. Absolute Maximum Ratings

Symbol	Parameter	Condition	Min	Typ	Max	Unit
T_{STG}	Storage temperature range		-40		150[1]	°C
T_S	Maximum soldering temperature	Latest IPC/JEDEC J-STD-020 Standard			260	°C
V_{DDMAX}	External main supply voltage		0		3.8	V
V_{IOPIN}	Voltage on any I/O pin		-0.3		V_{DD}+0.3	V

[1] Based on programmed devices tested for 10000 hours at 150ºC. Storage temperature affects retention of preprogrammed calibration values stored in flash. Please refer to the Flash section in the Electrical Characteristics for information on flash data retention for different temperatures.

3.3 General Operating Conditions

3.3.1 General Operating Conditions

Table 3.2. General Operating Conditions

Symbol	Parameter	Min	Typ	Max	Unit
T_{AMB}	Ambient temperature range	-40		85	°C
V_{DDOP}	Operating supply voltage	1.98		3.8	V
f_{APB}	Internal APB clock frequency			48	MHz
f_{AHB}	Internal AHB clock frequency			48	MHz

3.3.2 Environmental

Table 3.3. Environmental

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{ESDHBM}	ESD (Human Body Model HBM)	T_{AMB}=25°C			2000	V
V_{ESDCDM}	ESD (Charged Device Model, CDM)	T_{AMB}=25°C			750	V

Latch-up sensitivity passed: ±100 mA/1.5 × V_{SUPPLY}(max) according to JEDEC JESD 78 method Class II, 85°C.

3.4 Current Consumption

Table 3.4. Current Consumption

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{EM0}	EM0 current. No prescaling. Running prime number calculation code from Flash. (Production test condition = 14 MHz)	48 MHz HFXO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		225	236	µA/MHz
		48 MHz HFXO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		225		µA/MHz
		28 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		226	238	µA/MHz
		28 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		227		µA/MHz
		21 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		228	240	µA/MHz
		21 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		229		µA/MHz
		14 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		230	243	µA/MHz
		14 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		231		µA/MHz
		11 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		232	245	µA/MHz
		11 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		233		µA/MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		238	250	µA/MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		238		µA/MHz

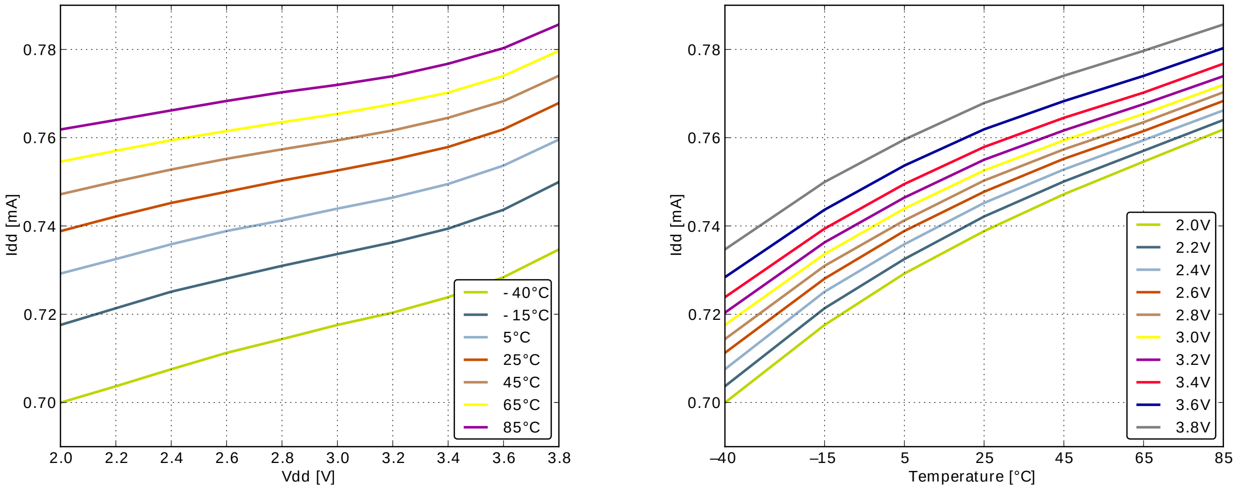


Figure 3.5. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 11MHz

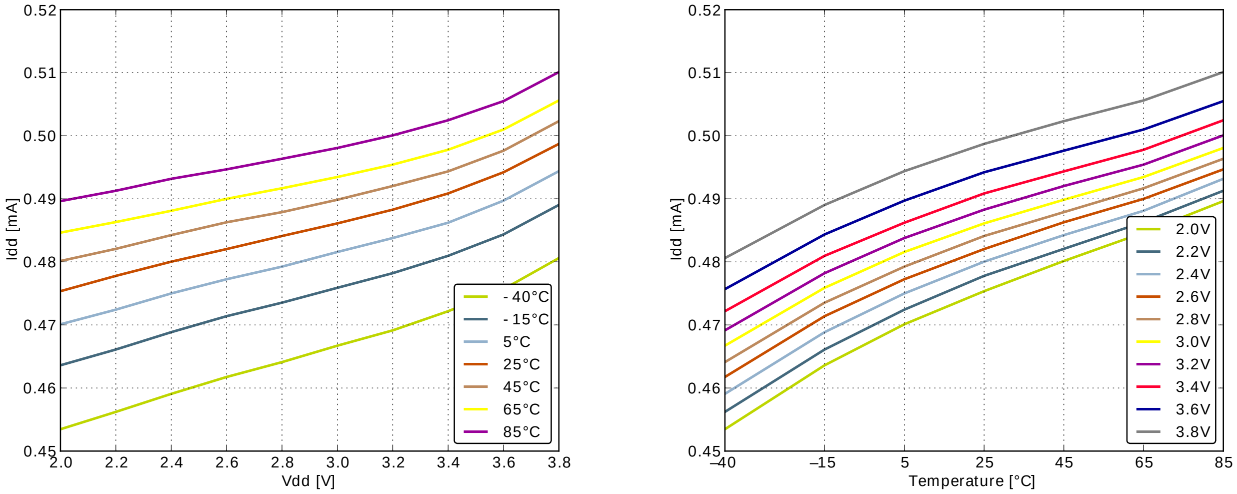


Figure 3.6. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 6.6MHz

3.6 Power Management

The EFM32WG requires the AVDD_x, VDD_DREG and IOVDD_x pins to be connected together (with optional filter) at the PCB level. For practical schematic recommendations, please see the application note, "AN0002 EFM32 Hardware Design Considerations".

Table 3.6. Power Management

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$V_{BODextthr-}$	BOD threshold on falling external supply voltage		1.74		1.96	V
$V_{BODextthr+}$	BOD threshold on rising external supply voltage			1.85	1.98	V
$V_{PORthr+}$	Power-on Reset (POR) threshold on rising external supply voltage				1.98	V
t_{RESET}	Delay from reset is released until program execution starts	Applies to Power-on Reset, Brown-out Reset and pin reset.		163		µs
$C_{DECOUPLE}$	Voltage regulator decoupling capacitor.	X5R capacitor recommended. Apply between DECOUPLE pin and GROUND		1		µF

3.7 Flash

Table 3.7. Flash

Symbol	Parameter	Condition	Min	Typ	Max	Unit
EC_{FLASH}	Flash erase cycles before failure		20000			cycles
RET_{FLASH}	Flash data retention	T_{AMB}<150°C	10000			h
		T_{AMB}<85°C	10			years
		T_{AMB}<70°C	20			years
t_{W_PROG}	Word (32-bit) programming time		20			µs
t_{PERASE}	Page erase time		20	20.4	20.8	ms
t_{DERASE}	Device erase time		40	40.8	41.6	ms
I_{ERASE}	Erase current				7[1]	mA
I_{WRITE}	Write current				7[1]	mA
V_{FLASH}	Supply voltage during flash erase and write		1.98		3.8	V

[1] Measured at 25°C

3.9 Oscillators

3.9.1 LFXO

Table 3.9. LFXO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LFXO}	Supported nominal crystal frequency			32.768		kHz
ESR_{LFXO}	Supported crystal equivalent series resistance (ESR)			30	120	kOhm
C_{LFXOL}	Supported crystal external load range		X[1]		25	pF
I_{LFXO}	Current consumption for core and buffer after startup.	ESR=30 kOhm, C_L=10 pF, LFXOBOOST in CMU_CTRL is 1		190		nA
t_{LFXO}	Start- up time.	ESR=30 kOhm, C_L=10 pF, 40% - 60% duty cycle has been reached, LFXOBOOST in CMU_CTRL is 1		400		ms

[1] See Minimum Load Capacitance (C_{LFXOL}) Requirement For Safe Crystal Startup in energyAware Designer in Simplicity Studio

For safe startup of a given crystal, the energyAware Designer in Simplicity Studio contains a tool to help users configure both load capacitance and software settings for using the LFXO. For details regarding the crystal configuration, the reader is referred to application note "AN0016 EFM32 Oscillator Design Consideration".

3.9.2 HFXO

Table 3.10. HFXO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{HFXO}	Supported nominal crystal Frequency		4		48	MHz
ESR_{HFXO}	Supported crystal equivalent series resistance (ESR)	Crystal frequency 48 MHz			50	Ohm
		Crystal frequency 32 MHz		30	60	Ohm
		Crystal frequency 4 MHz		400	1500	Ohm
g_{mHFXO}	The transconductance of the HFXO input transistor at crystal startup	HFXOBOOST in CMU_CTRL equals 0b11	20			mS
C_{HFXOL}	Supported crystal external load range		5		25	pF
I_{HFXO}	Current consumption for HFXO after startup	4 MHz: ESR=400 Ohm, C_L=20 pF, HFXOBOOST in CMU_CTRL equals 0b11		85		µA
		32 MHz: ESR=30 Ohm, C_L=10 pF, HFXOBOOST in CMU_CTRL equals 0b11		165		µA
t_{HFXO}	Startup time	32 MHz: ESR=30 Ohm, C_L=10 pF, HFXOBOOST in CMU_CTRL equals 0b11		400		µs

Symbol	Parameter	Condition	Min	Typ	Max	Unit
	and ADC core in NORMAL mode					
	Startup time of reference generator and ADC core in KEEPADCWARM mode			1		µs
SNR_{ADC}	Signal to Noise Ratio (SNR)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		59		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		1 MSamples/s, 12 bit, single ended, V_{DD} reference		65		dB
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		60		dB
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		65		dB
		1 MSamples/s, 12 bit, differential, 5V reference		54		dB
		1 MSamples/s, 12 bit, differential, V_{DD} reference		67		dB
		1 MSamples/s, 12 bit, differential, $2xV_{DD}$ reference		69		dB
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		62		dB
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		200 kSamples/s, 12 bit, single ended, V_{DD} reference		67		dB
		200 kSamples/s, 12 bit, differential, internal 1.25V reference		63		dB
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differential, V_{DD} reference	63	66		dB
		200 kSamples/s, 12 bit, differential, $2xV_{DD}$ reference		70		dB
$SINAD_{ADC}$	SIgnal-to-Noise And Distortion-ratio (SINAD)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		58		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		62		dB
		1 MSamples/s, 12 bit, single ended, V_{DD} reference		64		dB
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		60		dB

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		64		dB
		1 MSamples/s, 12 bit, differential, 5V reference		54		dB
		1 MSamples/s, 12 bit, differential, V_{DD} reference		66		dB
		1 MSamples/s, 12 bit, differential, $2xV_{DD}$ reference		68		dB
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		61		dB
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		65		dB
		200 kSamples/s, 12 bit, single ended, V_{DD} reference		66		dB
		200 kSamples/s, 12 bit, differential, internal 1.25V reference		63		dB
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differential, V_{DD} reference	62	66		dB
		200 kSamples/s, 12 bit, differential, $2xV_{DD}$ reference		69		dB
$SFDR_{ADC}$	Spurious-Free Dynamic Range (SFDR)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		64		dBc
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		76		dBc
		1 MSamples/s, 12 bit, single ended, V_{DD} reference		73		dBc
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		66		dBc
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		77		dBc
		1 MSamples/s, 12 bit, differential, V_{DD} reference		76		dBc
		1 MSamples/s, 12 bit, differential, $2xV_{DD}$ reference		75		dBc
		1 MSamples/s, 12 bit, differential, 5V reference		69		dBc
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		75		dBc
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		75		dBc
		200 kSamples/s, 12 bit, single ended, V_{DD} reference		76		dBc

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1, Unity Gain		13	25	µA
G_{OL}	Open Loop Gain	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		101		dB
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		98		dB
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		91		dB
GBW_{OPAMP}	Gain Bandwidth Product	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		6.1		MHz
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		1.8		MHz
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		0.25		MHz
PM_{OPAMP}	Phase Margin	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0, C_L=75 pF		64		°
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1, C_L=75 pF		58		°
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1, C_L=75 pF		58		°
R_{INPUT}	Input Resistance			100		Mohm
R_{LOAD}	Load Resistance		200			Ohm
I_{LOAD_DC}	DC Load Current				11	mA
V_{INPUT}	Input Voltage	OPAxHCMDIS=0	V_{SS}		V_{DD}	V
		OPAxHCMDIS=1	V_{SS}		V_{DD}-1.2	V
V_{OUTPUT}	Output Voltage		V_{SS}		V_{DD}	V
V_{OFFSET}	Input Offset Voltage	Unity Gain, $V_{SS}<V_{in}<V_{DD}$, OPAxHCMDIS=0	-13	0	11	mV
		Unity Gain, $V_{SS}<V_{in}<_{DD}$-1.2, OPAxHCMDIS=1		1		mV
V_{OFFSET_DRIFT}	Input Offset Voltage Drift				0.02	mV/°C
SR_{OPAMP}	Slew Rate	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		3.2		V/µs
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		0.8		V/µs
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		0.1		V/µs
N_{OPAMP}	Voltage Noise	V_{out}=1V, RESSEL=0, 0.1 Hz<f<10 kHz, OPAx-HCMDIS=0		101		μV_{RMS}
		V_{out}=1V, RESSEL=0, 0.1 Hz<f<10 kHz, OPAx-HCMDIS=1		141		μV_{RMS}

Figure 3.34. OPAMP Negative Power Supply Rejection Ratio

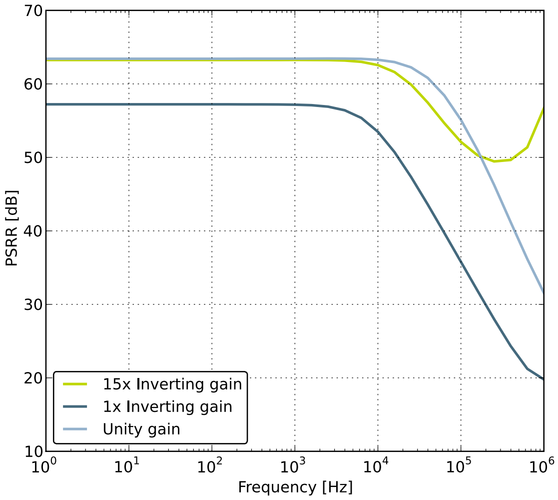


Figure 3.35. OPAMP Voltage Noise Spectral Density (Unity Gain) V_{out}=1V

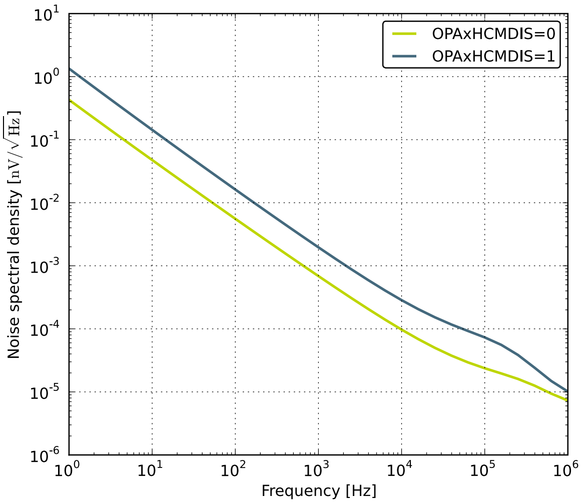


Figure 3.36. OPAMP Voltage Noise Spectral Density (Non-Unity Gain)

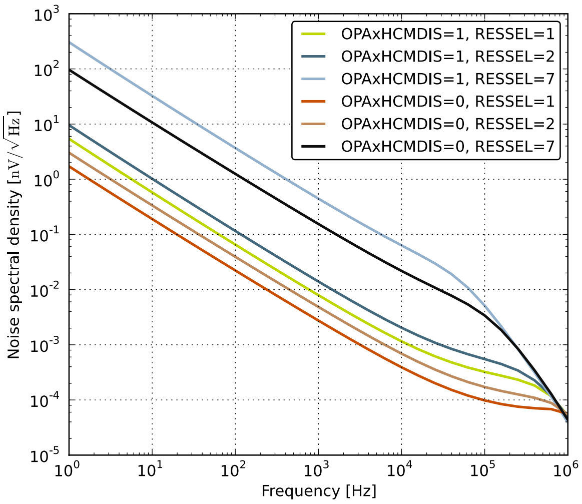


Figure 3.41. EBI Read Enable Related Timing Requirements

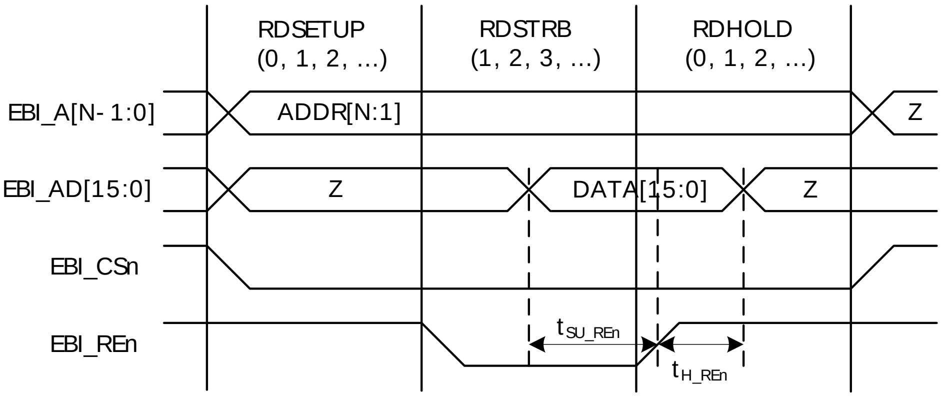


Table 3.23. EBI Read Enable Related Timing Requirements

Symbol	Parameter	Min	Typ	Max	Unit
t_{SU_REn} [1 2 3 4]	Setup time, from EBI_AD valid to trailing EBI_REn edge	37			ns
t_{H_Ren} [1 2 3 4]	Hold time, from trailing EBI_REn edge to EBI_AD invalid	-1			ns

[1] Applies for all addressing modes (figure only shows D16A8).

[2] Applies for both EBI_REn and EBI_NANDREn (figure only shows EBI_REn)

[3] Applies for all polarities (figure only shows active low signals)

[4] Measurement done at 10% and 90% of V_{DD} (figure shows 50% of $_{VDD}$)

Figure 3.42. EBI Ready/Wait Related Timing Requirements

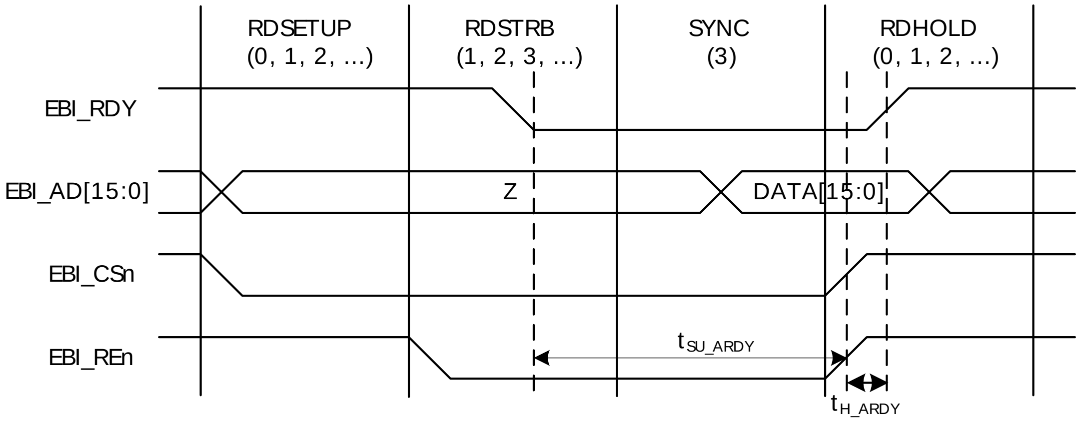


Table 3.24. EBI Ready/Wait Related Timing Requirements

Symbol	Parameter	Min	Typ	Max	Unit
t_{SU_ARDY} [1 2 3 4]	Setup time, from EBI_ARDY valid to trailing EBI_REn, EBI_WEn edge	$37 + (3 * t_{HFCORECLK})$			ns

Symbol	Parameter	Min	Typ	Max	Unit
t_{H_ARDY} [1] [2] [3] [4]	Hold time, from trailing EBI_REn, EBI_WEn edge to EBI_ARDY invalid	$-1 + (3 * t_{HFCORECLK})$			ns

[1] Applies for all addressing modes (figure only shows D16A8.)
[2] Applies for EBI_REn, EBI_WEn (figure only shows EBI_REn)
[3] Applies for all polarities (figure only shows active low signals)
[4] Measurement done at 10% and 90% of V_{DD} (figure shows 50% of $_{VDD}$)

3.16 I2C

Table 3.25. I2C Standard-mode (Sm)

Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		100[1]	kHz
t_{LOW}	SCL clock low time	4.7			µs
t_{HIGH}	SCL clock high time	4.0			µs
$t_{SU,DAT}$	SDA set-up time	250			ns
$t_{HD,DAT}$	SDA hold time	8		3450[2,3]	ns
$t_{SU,STA}$	Repeated START condition set-up time	4.7			µs
$t_{HD,STA}$	(Repeated) START condition hold time	4.0			µs
$t_{SU,STO}$	STOP condition set-up time	4.0			µs
t_{BUF}	Bus free time between a STOP and a START condition	4.7			µs

[1] For the minimum HFPERCLK frequency required in Standard-mode, see the I2C chapter in the EFM32WG Reference Manual.
[2] The maximum SDA hold time ($t_{HD,DAT}$) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}).
[3] When transmitting data, this number is guaranteed only when I2Cn_CLKDIV < ((3450*10^{-9} [s] * $f_{HFPERCLK}$ [Hz]) - 4).

Table 3.26. I2C Fast-mode (Fm)

Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		400[1]	kHz
t_{LOW}	SCL clock low time	1.3			µs
t_{HIGH}	SCL clock high time	0.6			µs
$t_{SU,DAT}$	SDA set-up time	100			ns
$t_{HD,DAT}$	SDA hold time	8		900[2,3]	ns
$t_{SU,STA}$	Repeated START condition set-up time	0.6			µs
$t_{HD,STA}$	(Repeated) START condition hold time	0.6			µs
$t_{SU,STO}$	STOP condition set-up time	0.6			µs
t_{BUF}	Bus free time between a STOP and a START condition	1.3			µs

[1] For the minimum HFPERCLK frequency required in Fast-mode, see the I2C chapter in the EFM32WG Reference Manual.
[2] The maximum SDA hold time ($t_{HD,DAT}$) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}).
[3] When transmitting data, this number is guaranteed only when I2Cn_CLKDIV < ((900*10^{-9} [s] * $f_{HFPERCLK}$ [Hz]) - 4).

Alternate	LOCATION							
Functionality	**0**	**1**	**2**	**3**	**4**	**5**	**6**	**Description**
US2_CLK	PC4	PB5						USART2 clock input / output.
US2_CS	PC5	PB6						USART2 chip select input / output.
US2_RX	PC3	PB4						USART2 Asynchronous Receive. USART2 Synchronous mode Master Input / Slave Output (MISO).
US2_TX	PC2	PB3						USART2 Asynchronous Transmit.Also used as receive input in half duplex communication. USART2 Synchronous mode Master Output / Slave Input (MOSI).

4.3 GPIO Pinout Overview

The specific GPIO pins available in *EFM32WG280* is shown in Table 4.3 (p. 67). Each GPIO port is organized as 16-bit ports indicated by letters A through F, and the individual pin on this port in indicated by a number from 15 down to 0.

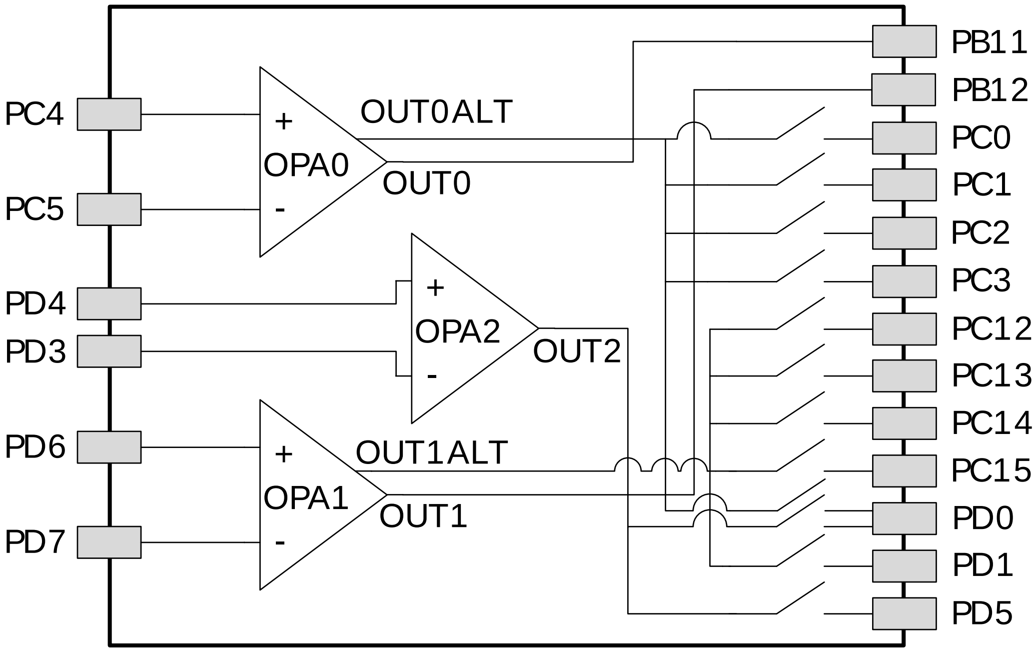
Table 4.3. GPIO Pinout

Port	Pin 15	Pin 14	Pin 13	Pin 12	Pin 11	Pin 10	Pin 9	Pin 8	Pin 7	Pin 6	Pin 5	Pin 4	Pin 3	Pin 2	Pin 1	Pin 0
Port A	PA15	PA14	PA13	PA12	PA11	PA10	PA9	PA8	PA7	PA6	PA5	PA4	PA3	PA2	PA1	PA0
Port B	-	PB14	PB13	PB12	PB11	PB10	PB9	PB8	PB7	PB6	PB5	PB4	PB3	PB2	PB1	PB0
Port C	PC15	PC14	PC13	PC12	PC11	PC10	PC9	PC8	PC7	PC6	PC5	PC4	PC3	PC2	PC1	PC0
Port D	-	-	-	PD12	PD11	PD10	PD9	PD8	PD7	PD6	PD5	PD4	PD3	PD2	PD1	PD0
Port E	PE15	PE14	PE13	PE12	PE11	PE10	PE9	PE8	PE7	PE6	PE5	PE4	PE3	PE2	PE1	PE0
Port F	-	-	-	-	-	-	PF9	PF8	PF7	PF6	PF5	PF4	PF3	PF2	PF1	PF0

4.4 Opamp Pinout Overview

The specific opamp terminals available in *EFM32WG280* is shown in Figure 4.2 (p. 67) .

Figure 4.2. Opamp Pinout



5 PCB Layout and Soldering

5.1 Recommended PCB Layout

Figure 5.1. LQFP100 PCB Land Pattern

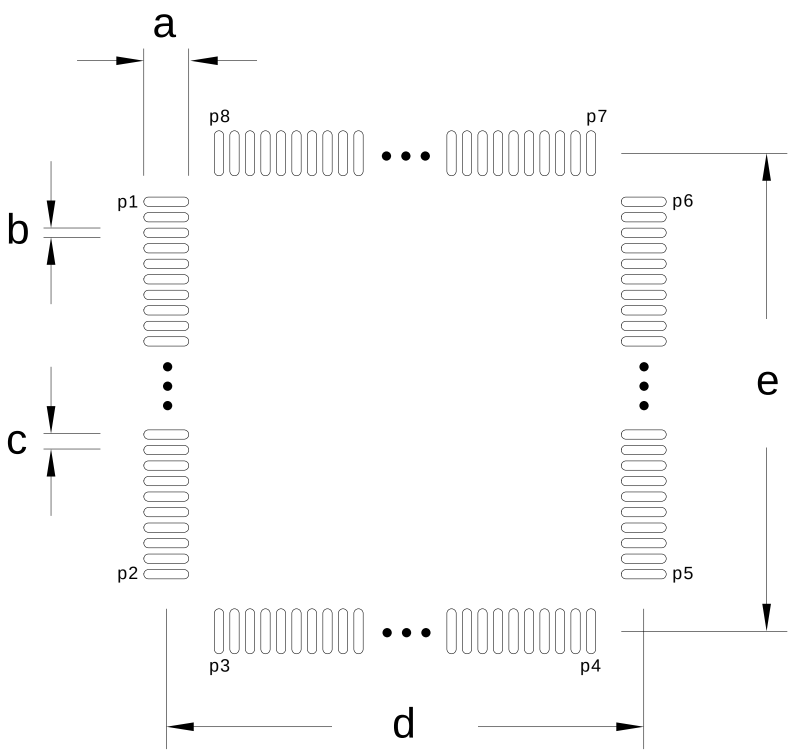


Table 5.1. QFP100 PCB Land Pattern Dimensions (Dimensions in mm)

Symbol	Dim. (mm)	Symbol	Pin number	Symbol	Pin number
a	1.45	P1	1	P6	75
b	0.30	P2	25	P7	76
c	0.50	P3	26	P8	100
d	15.40	P4	50	-	-
e	15.40	P5	51	-	-

Figure 5.2. LQFP100 PCB Solder Mask

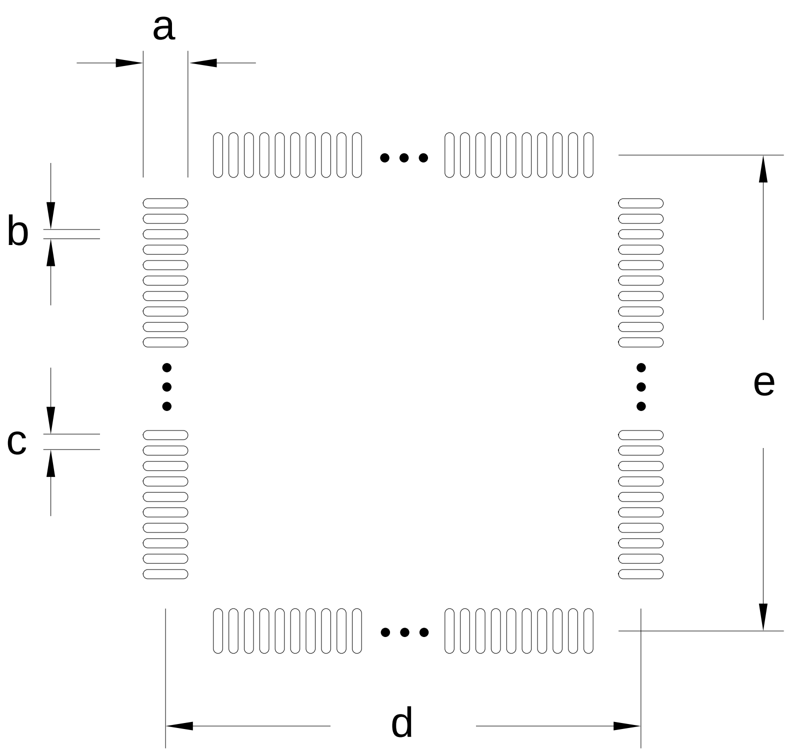


Table 5.2. QFP100 PCB Solder Mask Dimensions (Dimensions in mm)

Symbol	Dim. (mm)
a	1.57
b	0.42
c	0.50
d	15.40
e	15.40

Figure 5.3. LQFP100 PCB Stencil Design

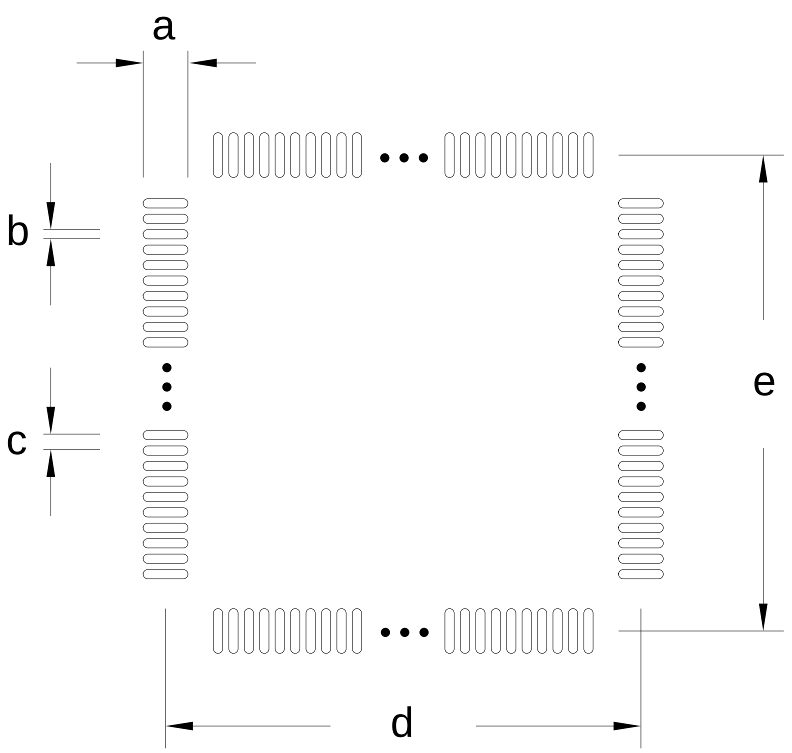


Table 5.3. QFP100 PCB Stencil Design Dimensions (Dimensions in mm)

Symbol	Dim. (mm)
a	1.35
b	0.20
c	0.50
d	15.40
e	15.40

1. The drawings are not to scale.
2. All dimensions are in millimeters.
3. All drawings are subject to change without notice.
4. The PCB Land Pattern drawing is in compliance with IPC-7351B.
5. Stencil thickness 0.125 mm.
6. For detailed pin-positioning, see Figure 4.3 (p. 68) .

5.2 Soldering Information

The latest IPC/JEDEC J-STD-020 recommendations for Pb-Free reflow soldering should be followed.

The packages have a Moisture Sensitivity Level rating of 3, please see the latest IPC/JEDEC J-STD-033 standard for MSL description and level 3 bake conditions.

7 Revision History

7.1 Revision 1.40

June 13th, 2014

Removed "Preliminary" markings.

Corrected single power supply voltage minimum value from 1.85V to 1.98V.

Added AUXHFRCO to blockdiagram and electrical characteristics.

Updated current consumption data.

Updated transition between energy modes data.

Updated power management data.

Updated GPIO data.

Updated LFRCO, HFRCO and ULFRCO data.

Updated ADC data.

Updated DAC data.

Updated OPAMP data.

Updated ACMP data.

Updated VCMP data.

Added EBI timing chapter.

7.2 Revision 1.31

November 21st, 2013

Updated figures.

Updated errata-link.

Updated chip marking.

Added link to Environmental and Quality information.

Re-added missing DAC-data.

7.3 Revision 1.30

September 30th, 2013

Added I2C characterization data.

Added SPI characterization data.

Corrected the DAC and OPAMP2 pin sharing information in the Alternate Functionality Pinout section.

Corrected the ADC resolution from 12, 10 and 6 bit to 12, 8 and 6 bit.

Updated the EM0 and EM1 current consumption numbers. Updated the the EM1 plots and removed the EM0 plots.

Updated Environmental information.

Updated trademark, disclaimer and contact information.

Other minor corrections.

7.4 Revision 1.20

June 28th, 2013

Updated power requirements in the Power Management section.

Removed minimum load capacitance figure and table. Added reference to application note.

Other minor corrections.

7.5 Revision 1.10

May 6th, 2013

Updated current consumption table and figures in Electrical characteristics section.

Other minor corrections.

7.6 Revision 1.00

September 11th, 2012

Updated the HFRCO 1 MHz band typical value to 1.2 MHz.

Updated the HFRCO 7 MHz band typical value to 6.6 MHz.

Other minor corrections.

7.7 Revision 0.95

May 3rd, 2012

Updated EM2/EM3 current consumption at 85°C.

7.8 Revision 0.90

February 27th, 2012

Initial preliminary release.

List of Figures